

VDS

 I_D

R_{DS(ON)TYP}

N-Channel Super Junction Power MOSFET III

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent RDS(ON) with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

Features

- •New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- ●100% Avalanche Tested
- ROHS compliant

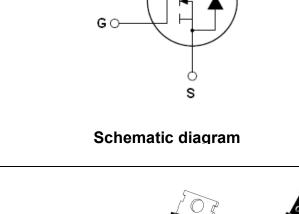
Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

Package Marking And Ordering Information

Device	Device Package	Marking	
NCE65T900D	TO-263	NCE65T900D	
NCE65T900	TO-220	NCE65T900	
NCE65T900F	TO-220F	NCE65T900F	

Table 1 Absolute Maximum Ratings (T_=25°C)



650

750

5

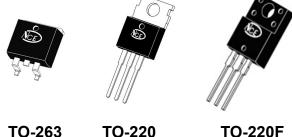
V

mΩ

А

D

С



TO-263

TO-220F

Parameter	Symbol	NCE65T900 NCE65T900D NCE65T900D		Unit
Drain-Source Voltage (VGs=0V)	Vds	650		V
Gate-Source Voltage (VDs=0V) AC (f>1 Hz)	Vgs	±30		V
Continuous Drain Current at Tc=25°C	I _{D (DC)}	5	5*	А
Continuous Drain Current at Tc=100°C	I _{D (DC)}	3	3*	А
Pulsed drain current (Note 1)	DM (pluse)	20	20*	А
Maximum Power Dissipation(Tc=25°C)	PD	46	29	W
Derate above 25°C		0.37	0.23	W/°C
Single pulse avalanche energy (Note2)	Eas	52		mJ
Avalanche current ^(Note 1)	I _{AR}	0.9		А
Repetitive Avalanche energy , t_{AR} limited by T_{jmax} (Note 1)	E _{AR}	0.14		mJ



NCE65T900D, NCE65T900, NCE65T900F

Parameter	Symbol	NCE65T900 NCE65T900D	NCE65T900F	Unit
Drain Source voltage slope, $V_{DS} \leqslant 480 V$,	dv/dt	50		V/ns
Reverse diode dv/dt, $V_{DS} \leqslant 480 V, I_{SD} < I_D$	dv/dt	1	5	V/ns
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55	+150	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	NCE65T900 NCE65T900D	NCE65T900F	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R _{thJC}	2.72	4.3	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R _{thJA}	62	80	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	650			V
Zero Gate Voltage Drain Current(Tc=25°C)	I _{DSS}	V _{DS} =650V,V _{GS} =0V			1	μA
Zero Gate Voltage Drain Current(Tc=125°C)	I _{DSS}	V _{DS} =650V,V _{GS} =0V			50	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	3		4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =2.5A		750	900	mΩ
Dynamic Characteristics						
Input Capacitance	C _{lss}			370		pF
Output Capacitance	C _{oss}	- V _{DS} =50V,V _{GS} =0V, - F=1.0MHz		25		pF
Reverse Transfer Capacitance	C _{rss}			0.5		pF
Total Gate Charge	Qg			10.5	15	nC
Gate-Source Charge	Q _{gs}	- V _{DS} =480V,I _D =5A, - V _{GS} =10V		2.6		nC
Gate-Drain Charge	Q _{gd}	- V _{GS} =10V		5.3		nC
Switching times						
Turn-on Delay Time	t _{d(on)}			7		nS
Turn-on Rise Time	tr	V _{DD} =380V,I _D =3A,		3		nS
Turn-Off Delay Time	t _{d(off)}	R _G =5Ω,V _{GS} =10V		52	62	nS
Turn-Off Fall Time	t _f			10	16	nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	– T _C =25°C			5	А
Pulsed Source-drain current(Body Diode)	I _{SDM}	- 1 _C -25 C			20	А
Forward on voltage	V _{SD}	Tj=25°C,I _{SD} =5A,V _{GS} =0V		0.9	1.2	V
Reverse Recovery Time	trr			210		nS
Reverse Recovery Charge	Qrr	Tj=25°C,I _F =2.5A,di/dt=100A/μs		0.66		uC
Peak reverse recovery current	Irrm			6.5		А

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25 $^\circ\!\mathrm{C},VDD$ =50V,VG=10V, R_G=25 Ω



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area for TO-220, TO-263

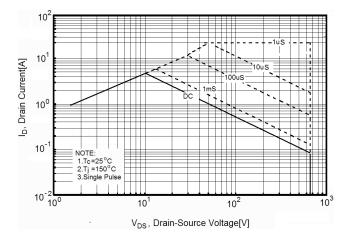


Figure3. Source-Drain Diode Forward Voltage

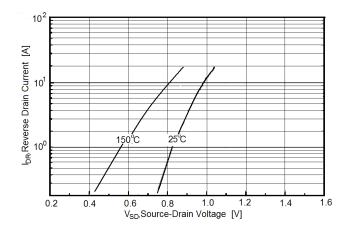


Figure5. Transfer characteristics

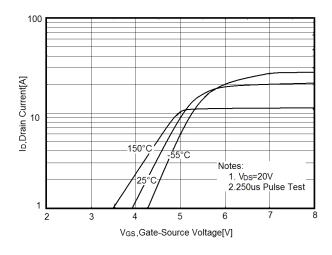


Figure 2. Safe operating area for TO-220F

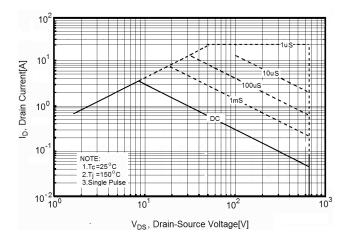


Figure4. Output characteristics

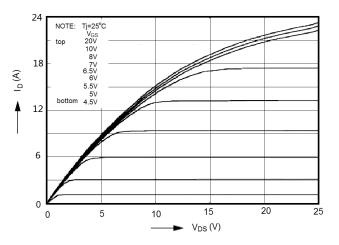


Figure6. Static drain-source on resistance

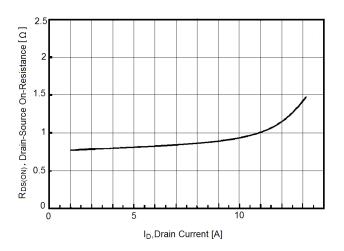




Figure7. R_{DS(ON)} vs Junction Temperature

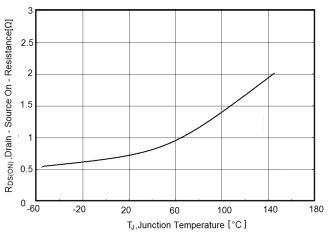


Figure9. Maximum I_D vs Junction Temperature

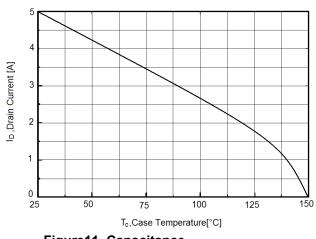


Figure11. Capacitance

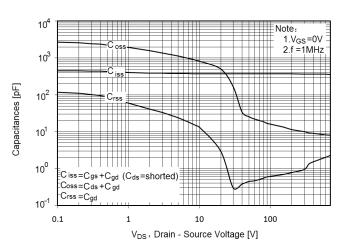


Figure8. BV_{DSS} vs Junction Temperature

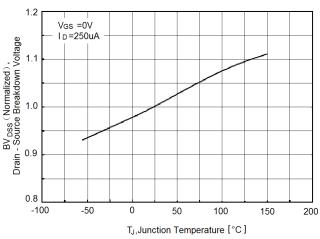


Figure10. Gate charge waveforms

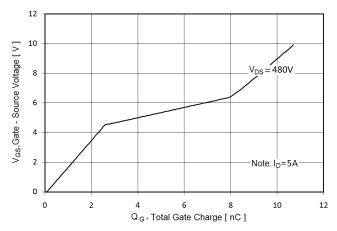
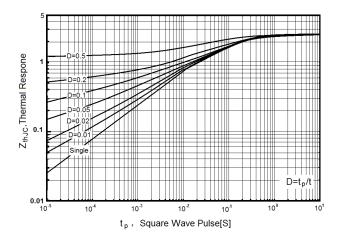


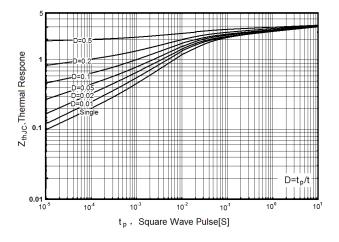
Figure12. Transient Thermal Impedance



Downloaded From Oneyac.com



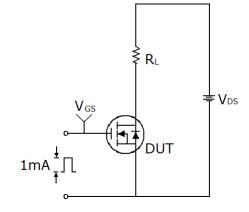
Figure13. Transient Thermal Impedance for TO-220F

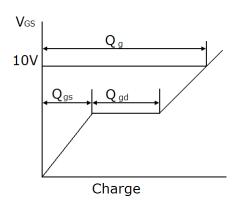




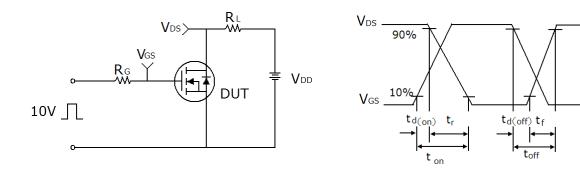
Test circuit

1) Gate charge test circuit & Waveform

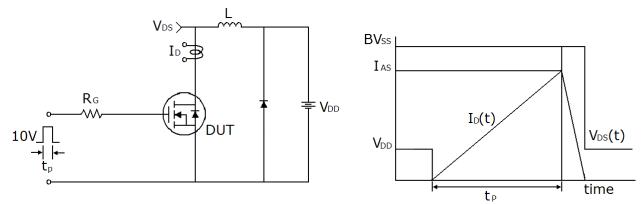




2) Switch Time Test Circuit:



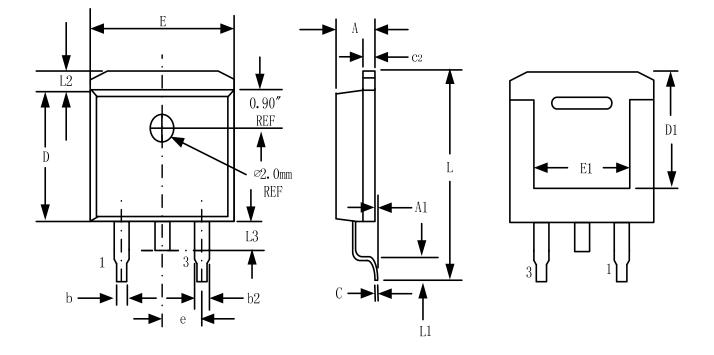
3) Unclamped Inductive Switching Test Circuit & Waveforms



Downloaded From Oneyac.com



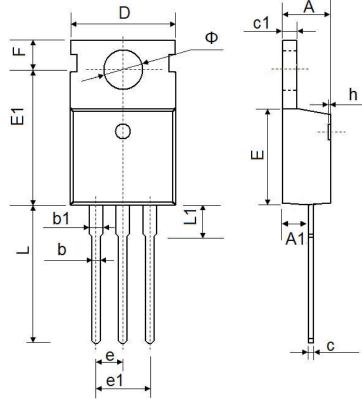
TO-263-3L Package Information

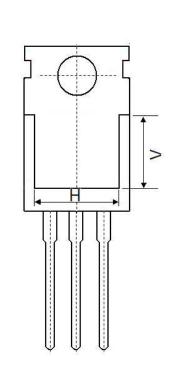


Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.32	4.57	0.170	0.180	
A1	-	0.25		0.010	
b	0.71	0.94	0.028	0.037	
b2	1.15	1.40	0.045	0.055	
С	0.46	0.61	0.018	0.024	
c2	1.22	1.40	0.048	0.055	
D	8.89	9.40	0.350	0.370	
D1	8.01	8.23	0.315	0.324	
E	10.04	10.28	0.395	0.405	
E1	7.88	8.08	0.310	0.318	
е	2.54	4 BSC	0.100	BSC	
L	14.73	15.75	0.580	0.620	
L1	2.29	2.79	0.090	0.110	
L2	1.15	1.39	0.045	0.055	
L3	1.27	1.77	0.050	0.070	



TO-220-3L-C Package Information

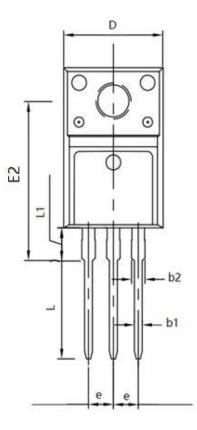


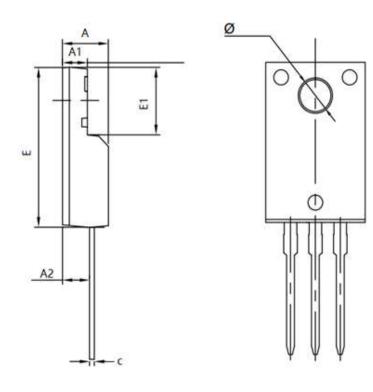


Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



TO-220F Package Information





Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.500	4.900	0.177	0.193	
A1	2.340	2.740	0.092	0.108	
A2	2.560	2.960	0.101	0.117	
b1	0.700	0.900	0.028	0.035	
b2	1.180	1.580	0.046	0.062	
С	0.400	0.600	0.016	0.024	
D	9.960	10.360	0.392	0.408	
E	15.670	15.970	0.617	0.629	
E1	6.500	6.900	0.256	0.272	
E2	15.500	16.100	0.610	0.634	
е	2.54	2.540 TYP) TYP	
Φ	3.080	3.280	0.121	0.129	
L	12.640	13.240	0.498	0.521	
L1	3.030	3.430	0.119	0.135	



ATTENTION:

- Any and all NCE products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your NCE representative nearest you before using any NCE products described or contained herein in such applications.
- NCE assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all NCE products described or contained herein.
- Specifications of any and all NCE products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- NCE Power Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all NCE products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of NCE Power Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. NCE believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the NCE product that you intend to use.
- This catalog provides information as of Mar. 2010. Specifications and information herein are subject to change without notice.

单击下面可查看定价,库存,交付和生命周期等信息

>>NCEPOWER(无锡新洁能)